

# 74V2T14

## TRIPLE SCHMITT INVERTER

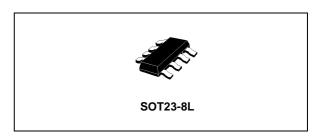
- HIGH SPEED:  $t_{PD} = 5.0$ ns (TYP.) at  $V_{CC} = 5$ V
- LOW POWER DISSIPATION:  $I_{CC} = 1\mu A(MAX.)$  at  $T_A = 25$ °C
- TYPICAL HYSTERESIS: V<sub>h</sub>=700mV at V<sub>CC</sub>=4.5V
- POWER DOWN PROTECTION ON INPUT
- SYMMETRICAL OUTPUT IMPEDANCE:  $|I_{OH}| = I_{OL} = 8\text{mA}$  (MIN) at  $V_{CC} = 4.5\text{V}$
- BALANCED PROPAGATION DELAYS: t<sub>PLH</sub> ≅ t<sub>PHL</sub>
- OPERATING VOLTAGE RANGE: V<sub>CC</sub>(OPR) = 4.5V to 5.5V
- IMPROVED LATCH-UP IMMUNITY

#### **DESCRIPTION**

The 74V2T14 is an advanced high-speed CMOS TRIPLE SCHMITT INVERTER fabricated with sub-micron silicon gate and double-layer metal wiring C<sup>2</sup>MOS technology.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output.

Power down protection is provided on input and 0 to 7V can be accepted on input with no regard to



#### **ORDER CODES**

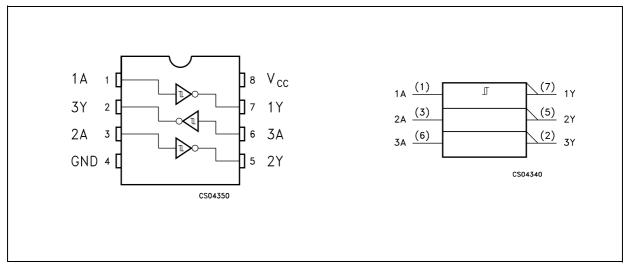
PACKAGE	T&R
SOT23-8L	74V2T14STR

the supply voltage. This device can be used to interface 5V to 3V. Pin configuration and function are the same as those of the 74V2T04 but the 74V2T14 has hysteresis.

This together with its schmitt trigger function allows it to be used on line receivers with slow rise/fall input signals.

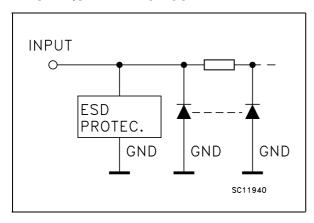
The input is equipped with protection circuits against static discharge, giving it ESD immunity and transient excess voltage.

#### PIN CONNECTION AND IEC LOGIC SYMBOLS



June 2003 1/7

#### **INPUT EQUIVALENT CIRCUIT**



#### **PIN DESCRIPTION**

PIN No	SYMBOL	NAME QND FUNCTION
1, 3, 6	1A, 2A, 3A	Data Inputs
7, 5, 2	1Y, 2Y, 3Y	Data Outputs
4	GND	Ground (0V)
8	V <sub>CC</sub>	Positive Supply Voltage

## **TRUTH TABLE**

Α	Y
L	Н
Н	L

#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 to +7.0	V
Vo	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	- 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
Io	DC Output Current	± 25	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 50	mA
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	260	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

### **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	4.5 to 5.5	V
V <sub>I</sub>	Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V <sub>CC</sub>	V
T <sub>op</sub>	Operating Temperature	-55 to 125	°C

#### **DC SPECIFICATIONS**

		1	est Condition	Value							
Symbol	Parameter	v <sub>cc</sub>		Т	T <sub>A</sub> = 25°C		-40 to	85°C	-55 to 125°C		Unit
		(V)		Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
V <sub>t+</sub>	High Level	4.5		0.9		2.0	0.9	2.0	0.9	2.0	V
	Threshold Voltage	5.5		1.1		2.0	1.1	2.0	1.1	2.0	V
V <sub>t-</sub>	Low Level	4.5		0.5		1.5	0.5	1.5	0.5	1.5	V
	Threshold Voltage	5.5		0.6		1.6	0.6	1.6	0.6	1.6	V
$V_{h}$	Hysteresis Voltage	4.5		0.4		1.4	0.4	1.4	0.4	1.4	V
		5.5		0.5		1.6	0.5	1.6	0.5	1.6	٧
V <sub>OH</sub>	High Level Output	4.5	I <sub>O</sub> =-50 μA	4.4	4.5		4.4		4.4		V
	Voltage	4.5	I <sub>O</sub> =-8 mA	3.94			3.8		3.7		
V <sub>OL</sub>	Low Level Output	4.5	I <sub>O</sub> =50 μA		0.0	0.1		0.1		0.1	V
	Voltage	4.5	I <sub>O</sub> =8 mA			0.36		0.44		0.55	
I <sub>I</sub>	Input Leakage Current	0 to 5.5	V <sub>I</sub> = 5.5V or GND			± 0.1		± 1.0		± 1.0	μΑ
Icc	Quiescent Supply Current	5.5	$V_I = V_{CC}$ or GND			1		10		20	μΑ
△lcc	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V <sub>CC</sub> or GND			1.35		1.5		1.5	mA

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

		Test Condition			Value								
Symbol	Parameter	v <sub>cc</sub> c	v <sub>cc</sub>	CC CL		Т	A = 25°	С	-40 to	85°C	-55 to	125°C	Unit
		(V)	(pF)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
t <sub>PLH</sub>	Propagation Delay	5.0 (*)	15			5.0	7.5	1.0	9.0	1.0	10.5	nc	
t <sub>PHL</sub>	Time	5.0 (*)	50			6.5	8.5	1.0	10.0	1.0	11.5	ns	

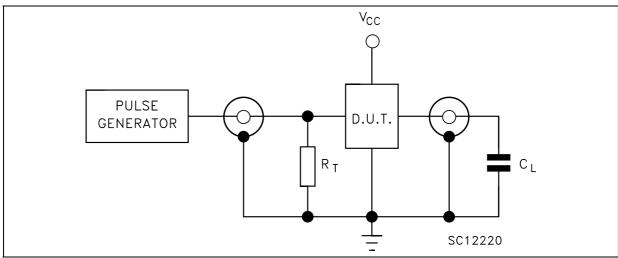
<sup>(\*)</sup> Voltage range is  $5.0V \pm 0.5V$ 

### **CAPACITIVE CHARACTERISTICS**

		Test Condition		Value						
Symbol	Parameter		T <sub>A</sub> = 25°C			-40 to	85°C	-55 to 125°C		Unit
			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
C <sub>IN</sub>	Input Capacitance			4	10		10		10	pF
C <sub>PD</sub>	Power Dissipation Capacitance (note 1)			14						pF

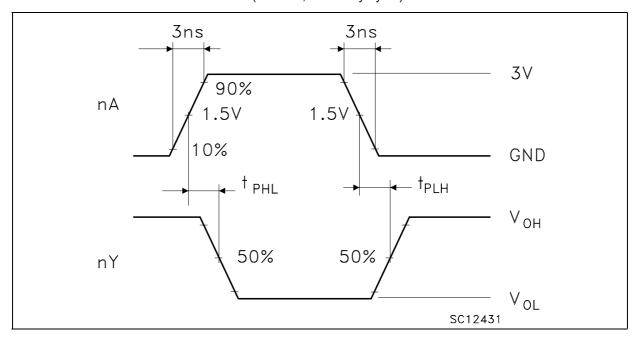
<sup>1)</sup>  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/3$ 

#### **TEST CIRCUIT**



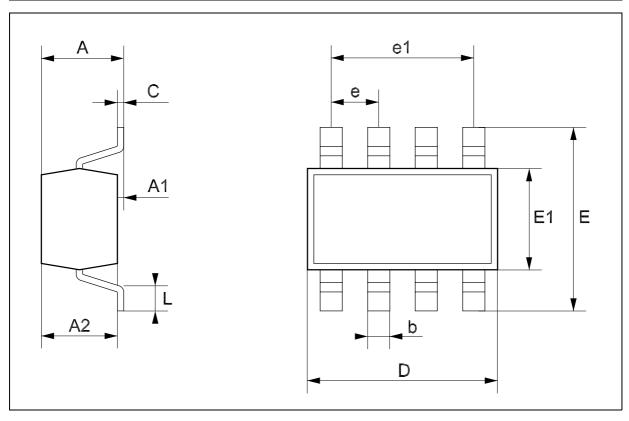
 $C_L$  = 15/50pF or equivalent (includes jig and probe capacitance)  $R_T$  =  $Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

## WAVEFORM: PROPAGATION DELAY (f=1MHz; 50% duty cycle)



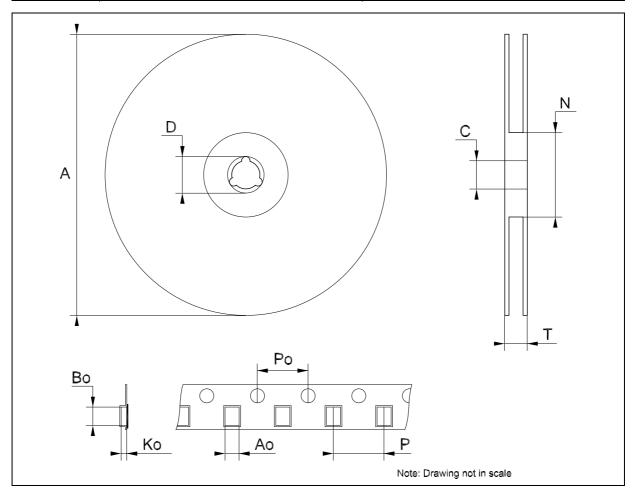
# **SOT23-8L MECHANICAL DATA**

DIM		mm.		mils					
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.			
А	0.90		1.45	35.4		57.1			
A1	0.00		0.15	0.0		5.9			
A2	0.90		1.30	35.4		51.2			
b	0.22		0.38	8.6		14.9			
С	0.09		0.20	3.5		7.8			
D	2.80		3.00	110.2		118.1			
E	2.60		3.00	102.3		118.1			
E1	1.50		1.75	59.0		68.8			
е	0	.65			25.6				
e1		1.95			76.7				
L	0.35		0.55	13.7		21.6			



# Tape & Reel SOT23-xL MECHANICAL DATA

DIM		mm.		inch				
DIM.	MIN.	TYP	MAX.	MIN.	TYP.	MAX.		
А			180			7.086		
С	12.8	13.0	13.2	0.504	0.512	0.519		
D	20.2			0.795				
N	60			2.362				
Т			14.4			0.567		
Ao	3.13	3.23	3.33	0.123	0.127	0.131		
Во	3.07	3.17	3.27	0.120	0.124	0.128		
Ko	1.27	1.37	1.47	0.050	0.054	0.0.58		
Ро	3.9	4.0	4.1	0.153	0.157	0.161		
Р	3.9	4.0	4.1	0.153	0.157	0.161		



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